

isc Silicon PNP Power Transistor
KSE350
DESCRIPTION

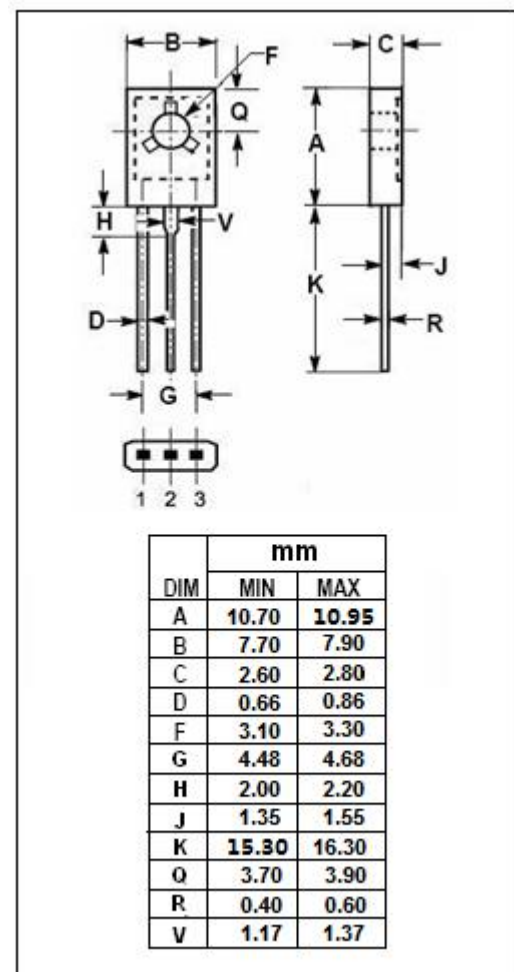
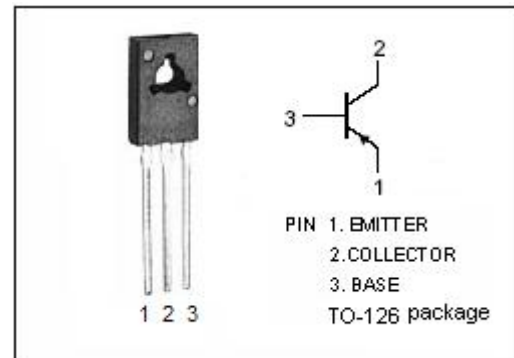
- High Collector-Emitter breakdown voltage
- Low Collector Saturation Voltage
- Complement to Type KSE340
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation


APPLICATIONS

- High voltage general purpose applications
- Suitable for transform

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	-300	V
V _{CEO}	Collector-Emitter Voltage	-300	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current-Continuous	-0.5	A
P _C	Collector Power Dissipation @ T _C =25°C	20	W
	Collector Power Dissipation @ T _a =25°C	1.3	
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



ELECTRICAL CHARACTERISTICS

 T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I _{CB0}	Collector Cutoff Current	V _{CB} = -300V; I _E = 0			-100	μ A
I _{EB0}	Emitter Cutoff Current	V _{EB} = -3V; I _C = 0			-100	μ A
h _{FE}	DC Current Gain	I _C =- 50mA; V _{CE} = -10V	30		240	

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